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**CHENG**(10) **Pub. No.: US 2023/0232610 A1**(43) **Pub. Date: Jul. 20, 2023**(54) **SEMICONDUCTOR STRUCTURE HAVING  
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The present disclosure provides a semiconductor structure having a fin structure. The semiconductor includes a substrate defined with an active region. A first gate structure is disposed in the active region and includes a dielectric material. A second gate structure is disposed in the active region and includes the dielectric material. A fin structure having a first top surface is arranged to alternate with the first gate structure and the second gate structure. The first gate structure has a second top surface and the second gate structure has a third top surface. The second top surface and the third top surface are lower than the first top surface.

